

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S40	1	(hugues near2 marchand or brendan near2 moran).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:14
S45	128	graded near5 (gan or algan or aluminum near2 nitride or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S44	11	(si or silicon) near10 substrate same graded near10 (nitride or gan or algan) and weeks.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S43	96	(si or silicon) near10 substrate same graded near10 (nitride or gan or algan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S42	102	buffer near5 (aln or aluminum near2 nitride) same (si or silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S34	78	buffer near5 (aln or aluminum near2 nitride) same (si or silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S27	112	graded near5 (gan or algan or aluminum near2 nitride or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S3	10	(si or silicon) near10 substrate same graded near10 (nitride or gan or algan) and weeks.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S2	88	(si or silicon) near10 substrate same graded near10 (nitride or gan or algan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:15
S46	81	graded near5 (gan or algan or aluminum near2 nitride or gallium near2 nitride) and (si or silicon) near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:16

S48	0	graded near5 buffer and bufer near10 (gan or gallium near2 nitride) near15 (si or silicon) near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:17
S47	21	graded near5 (gan or algan or aluminum near2 nitride or gallium near2 nitride) near15 (si or silicon) near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 01:17
S49	12	graded near5 buffer and buffer near10 (gan or gallium near2 nitride) near15 (si or silicon) near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 17:33
L2	5	1 and grad\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 17:34
L1	30	US-5880485-\$.DID. OR US-6153010-\$. DID. OR US-6180270-\$.DID. OR US-6291319-\$.DID. OR US-6328796-\$. DID. OR US-6358770-\$.DID. OR US-6391748-\$.DID. OR US-6420197-\$. DID. OR US-6440823-\$.DID. OR US-6459712-\$.DID. OR US-6524932-\$. DID. OR US-6548333-\$.DID. OR US-6610144-\$.DID. OR US-6707074-\$. DID. OR US-6765240-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 17:34
S41	2	(hugues near2 marchand or brendan near2 moran).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 17:36
L3	2	(hugues near2 marchand or brendan near2 moran).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 17:36